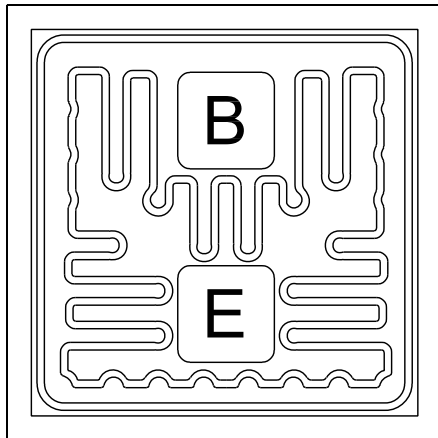


PROCESS DETAILS

Process	Epitaxial Planar
Die Size	18 x 18 MILS
Die Thickness	7.1 MILS
Base Bonding Pad Area	3.8 x 3.8 MILS
Emitter Bonding Pad Area	3.8 x 3.8 MILS
Top Side Metalization	Al/Si - 30,000Å
Back Side Metalization	Au - 12,000Å

Geometry



BACKSIDE COLLECTOR R0

GROSS DIE PER 5 INCH WAFER

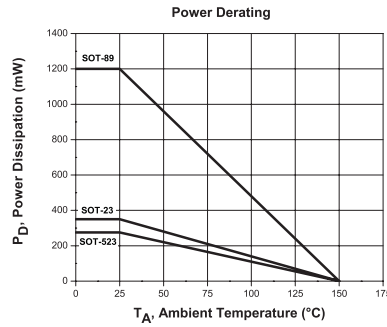
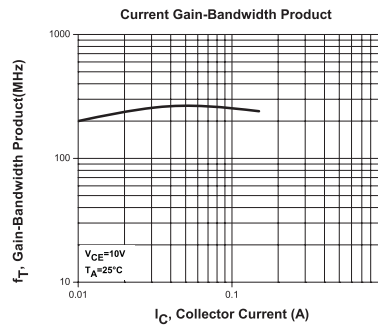
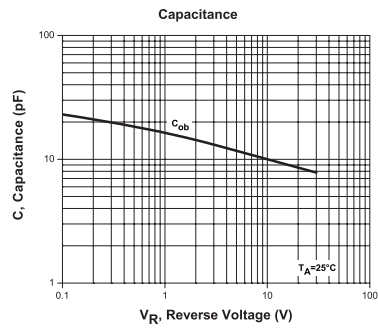
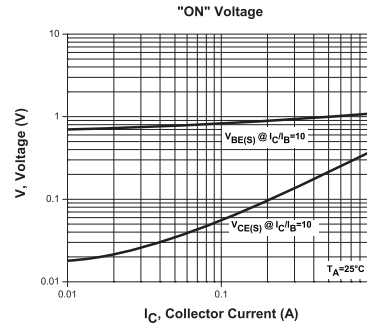
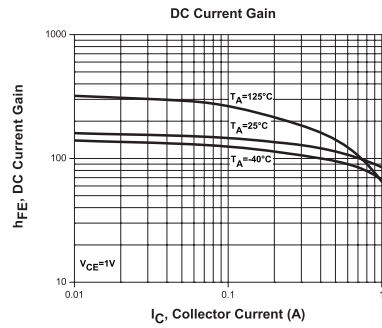
54,330

PRINCIPAL DEVICE TYPES

CMLT7410
CMPT7410
CMST7410
CMUT7410

145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
www.centrasemi.com

R1 (12-August 2008)



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